VO_2 : a two-uid incoherent m etal?

M.S.Laad¹, L.C $racc^2$ and E.M uller-H artm ann^2

 1 D epartm ent of P hysics, Loughborough U niversity, LE 11 3T U , U K

² Institut fur Theoretische Physik, Universitat zu Koln, 77 Zulpicher Strasse, D-50937 Koln, Germany

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W e present ab initio LDA + DMFT results for the many-particle density of states of VO₂ on the metallic side of the strongly rst-order (T-driven) insulator metal transition. In strong contrast to LDA predictions, there is no remnant of even correlated Fermi liquid behavior in the correlated metal. Excellent quantitative agreement with published photoemission and X-ray absorption experiments is found in the metallic phase. We argue that the absence of FL-quasiparticles provides a natural explanation for the bad-metallic transport for T > 340 K. Based on this agreement, we propose that the I-M transition in VO₂ is an orbital-selective M ott transition, and point out the relevance of orbital resolved one-electron and optical spectroscopy to resolve this outstanding issue.

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M etal-insulator transitions (M IT) in early-transition m etal oxides (TMO) are classic examples of correlationdriven M ott-H ubbard transitions [1]. Strong multiorbital correlations in the real crystal structure (RCS) have turned out to be indispensable for a quantitative description of the M IT in these cases [2].

A detailed understanding of the above cases is still som ewhat elusive. In particular, it is still unclear whether the M IT is orbital selective, i.e., whether di erent orbital-resolved densities-of-states (DOS) are gapped (driving the M ott insulating state) at di erent values of U;U⁰ (de ned below) or whether there is a single (common) M ott transition at a critical interaction strength [3,4]. C on icting results, even for the same system, and within the same (d = 1) approximation [4] have been obtained, necessitating m ore work to resolve this issue.

In this communication, we address precisely this issue in vanadium dioxide (VO₂). Using the state-of-the-art LDA+DMFT [5] technique, we rst show how excellent quantitative agreement with the full, local one-electron spectral function is achieved using LDA+DMFT (PT). We then build on this agreement, claiming that the MIT in VO₂ is orbital selective, and represents a concrete, ab initio realization of the two-uid scenario for MIT in strongly correlated system s.

 VO_2 shows a spectacular M IT at T = 340 K from a low-T m onoclinic, M ott insulating phase with spin dim erization along the crystallographic c-axis to a local m om ent param agnetic m etallic phase. This T-driven M IT has attracted intense scrutiny: because of the additional com plication of the antiferroelectric displacem ent of the VO_6 octahedra in a correlated system, an unam biguous characterization of the M IT (relative in portance of M ott-H ubbard versus P eierls dim erization) is som ew hat di cult. Various observations have been cited in support of both scenarios [1], and theoretical m odels detailing the im portance of these e ects have been proposed [6,7].

One-electron spectroscopies constitute a reliable ngenprint of the changes in the single-particle spectral

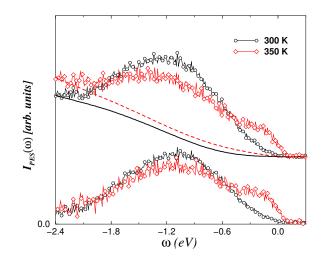


FIG. 1. Photoem ission spectrum of VO_2 across the metal-insulator transition, from [11]. Top: raw data; bottom: with the O -2p background subtracted in a way indicated by the region below the solid (300 K) and dashed (350 K) lines.

function (and hence those in the correlated electronic structures) across a phase transition. M any papers have studied the M IT in VO2 by photoelectron-and X-ray absorption spectroscopy (PES and XAS) [8{10]. A perusal of the available literature requires care to pinpoint robust features (weakly dependent on incident photon energy); in what follows, we use only those published data which satisfy this criterion in order to make comparison with theory. U sually, the experiments have been carried out with low incident photon energies (50 70 eV) except in Ref. [11] (1200 eV). However, the main features, namely: (i) a broad step-like feature crossing E_F in the R phase, (ii) the \lower Hubbard band" centered at 1 eV, and (iii) the huge 0 2p-band contribution from 2 eV, seem to be roughly consistent in all these m easurem ents. U pon subtraction of the 0-2p contribution, the corresponding \Vanadium " t2g DOS shows noticeably more spectral weight at low erenergies relative to that at 1 eV (Fig.1). In this context, great care has to be taken, as, in view of the dynam ical transfer of spectral weight over large energy scales characteristic of a correlated system, it is not a priori clear whether the subtracted \background" contains signi cant intrinsic strong correlation (continuum) contributions. A dditional subtraction due to surface contributions to the incoherent part [11] results in noticeably m ore spectral weight at low energy com pared to that at 1:5 eV.

W ith these caveats, a consistent picture of the changes in the actual electronic structure across the M IT seems to emerge. First, the transition is clearly driven by the dynam icaltransfer of spectral weight from high to low energy over a large energy scale of 0 (2 eV), characteristic of a M ott-H ubbard scenario. Second, in the m etallic (R) phase, there is no sem blance of a Ferm i liquid-like peak at low energy: rather, the low -energy feature is m ore-or-less incoherent. This is in good accord with the high resistivity in the (metallic) R phase, as also with the linearin-T dependence without saturation upto 900 K [12]. It is natural to postulate a common electronic scattering mechanism leading to such observations. In the insulating (I) phase, clear evidence of insulating gap form ation is visible in PES.From Fig. 3 of Ref. [11], we estimate the gap value E_G ' 02 03 eV, consistent with that extracted from optical data [13].

The XAS data probe the unoccupied part of the full spectral function, and show a number of interesting features in VO₂. First, we notice that the XAS intensity is much larger (for 0 ! 2:0 eV) than the XPS intensity (for 2:0 ! 0 eV). Second, the broad low-energy \step-like" feature seems a actually to be the lower part of the intense feature in XAS pulled below E_F , and is not a therm ally sm eared correlated Ferm i liquid resonance. A sm entioned above, this ts in nicely with the transport data; in any case, we do not expect a quasicoherent FL scale to survive beyond very low tem peratures in a correlated system close to a M I transition.

B eginning with the LDA bandstructure of VO $_2$ in the m onoclinic crystal structure corresponding to the insulating phase [14], with subtraction of terms to avoid double-counting of interactions treated on average by LDA, the one-electron H am iltonian is,

$$H_{LDA}^{(0)} = \begin{bmatrix} X & & X \\ k & k \end{bmatrix} c_{k}^{Y} c_{k} + \begin{bmatrix} X & & & \\ i & n_{i} \end{bmatrix} (1)$$

where ${}^0_1 = {}_i$ U (n $\frac{1}{2}$) + $\frac{1}{2}$ J_H (n 1). Here, U;U⁰;J_H are the C oulomb interactions in the t_{2g} shell, and are de ned below. The lowest lying xy (in the M notation) band is the most heavily populated, while the yz zx bands are less populated. The bondingantibonding splitting [14] is clearly visible in the results, which also show that the total bandwidth is about W ' 2:3 eV, contrary to m uch sm aller previous [7] estim ates based on m odel calculations. Sophisticated LDA calculations do yield a m iniscule, alm ost zero-gap, P eierls insulator [6], but obviously do not reproduce the M ott insulator. As emphasized by Zylbersteyn et al. [7], it is inconceivable that the antiferroelectric distortion alone could open up a charge gap ($E_{\rm G}$ ' 0.6 eV), requiring proper incorporation of correlation e ects.

Including multi-orbital correlations, the full H am iltonian is

$$H = H_{LDA}^{(0)} + U \qquad n_{i} * n_{i \#} + U \qquad n_{i} n_{i 0}$$

$$X \qquad i \qquad i^{0}$$

$$J_{H} \qquad S_{i} \qquad S_{i} \qquad S_{i} \qquad (2)$$

This multi-orbital Hubbard model is solved using LDA + DMFT (IPT) [3]. Accurate low - and high energy behavior is ensured by requiring strict num erical com pliance with the Friedel-Luttinger sum rule (low-energy) and the rst three moments of the DOS (high energy). In our approach, the M I transition is driven by the large change in the dynam ical spectral weight transfer accom panying sm all changes in the renorm alized antiferroelectric displacement in the correlated picture. Hence the transition is of the M ott-H ubbard type, but the antiferroelectric coupling also plays an important role: in fact, it acts like an \external eld" in the orbital (t_{2q}) sector. Changes in this external eld drives changes in orbital occupation on the one hand, and results in a lowering of the free energy (of the metallic solution) as a function of , stabilizing the m etallic solution at a critical , as found in the calculations. Com parison value of with data for the insulating state requires incorporation of the c-axis dim erization [7] into our DMFT procedure, and requires extension of the present approach. Hence, we focus only on the metallic state in what follows.

W e now com pare our theoretical results to experim ent, showing how excellent quantitative agreement with the full one-electron spectrum in the metallic (R) phase is achieved in this picture. The calculations were done at $T_1 = 150 \text{ K} < T_{M T}$ (I-phase) and $T_2 = 370 \text{ K} > T_{M T}$ (M -phase). We used parameter values identical to those used in Ref. [3]: the LDA bandwidth W ' 2:0 eV, and interactions specied by U ' 5:0 eV; $J_{H} = 1:0$ eV and U⁰ ′ (U $2J_{\rm H}$) = 3:0 eV for the I-phase. To account for reduction of the e ective interaction due to dynamical (selfconsistent) screening processes relevant upon the transition to the M -phase, we use reduced valuesofU ' 4:6 eV;U⁰' 2:6 eV in the M -phase, while J_H, being alm ost unscreened, is kept xed. As described in Ref. [3], the M IT in our picture results from large changes in dynam icaltransfer of spectral weight from high-to low energies following small changes in the renormalized antiferroelectric distortion in VO_2 .

In Fig.2, we show the theory-experim ent com parison for the total (photoem ission + X-ray absorption) intensity, I_{total} (!) for the m etallic (R) phase. Rem arkably,

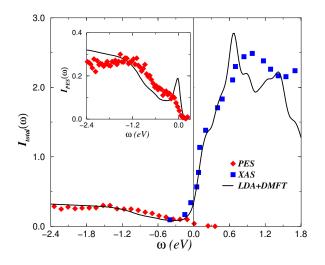


FIG.2. Comparison of theoretical (LDA + DMFT) result for the total one-electron spectral function in the metallic phase of VO₂ to the experimental results taken from [11] (for PES) and from [9] (for XAS). The inset shows a blow-up of the PES spectrum. The theoretical result is compared with the raw data without subtraction of the O-2p and surface contribution. Subtraction of the surface contribution as in [11] would lead to even better agreement, as explained in the text.

the agreem ent between theory and experim ent in the region 2:4 ! 0:8 eV is excellent. W e have not tried to t the data for ! < 2:4 eV and ! > 0:8 eV because only part of the 0 –2p and e_g bands of V projected onto the t_{2q} states have been included in our LDA+DMFT calculation. We emphasize that even better agreement could have been obtained if the subtraction of the surface contributions would have been carried out without taking out the O -2p \background" in Fig. 1. This would have had the e ect of increasing the weight in the region 0:3 1 0 eV and decreasing the weight in the region 1:8 1 0:5 eV [11], further improving the t.

Several features of the experim ental spectra are readily interpreted in the light of the theoretical calculation. First, most of the low -energy spectral weight actually corresponds to (largely incoherent) electronic states close to the minimum of the pseudogap in the spectral function. There is no indication of even a strongly renorm alized FL-like resonance. The DOS at $E_F = 0 \text{ eV}$ is drastically reduced compared to the LDA value [14], in excellent agreem ent with the data, and in full accord with the bad m etallic resistivity in the R phase. The lower Hubbard band feature around 1:2 eV is reproduced very well, as is the shoulder-like feature at 0.3 eV in XAS. In [3], we found excellent agreem ent with the optical e ective mass, m = m_b ' 3:0, a value that is also consistent with the observed enhancem ent of the param agnetic spin susceptibility in the R phase. Thus, these results represent a quantitatively accurate description of basic spectroscopic and therm odynam ic results for the m etallic state.

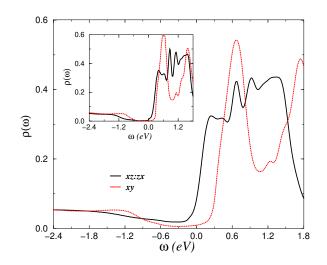


FIG.3. O ibital-resolved one electron spectral functions for the m etallic phase of VO₂ (m ain fram e) and for the insulating phase without spin dim erization (inset). Only the d_{yz}_{zx} orbital DOS crosses E_F in the m etallic phase; the d_{xy} DOS still shows M ott-H ubbard insulating features, showing the \two-uid" character of the M IT in VO₂.

A m ed with this agreem ent, we proceed to analyze the M II in VO_2 in more microscopic detail. Fig. 3 shows the orbital-resolved DOS for the metallic phase. Clearly, zx DOS gives rise to the metallic behavonly the yz ior; the xy orbital DOS is still gapped at a value close to that for the (undim erized, but this is not the real low est state in the I phase) param agnetic insulating state. This observation, constituting an explicit manifestation of the two-uid scenario for the M ott transition in VO₂ driven by multi-orbital correlations, is the central result of our analysis. If con med by experiment, this result would imply concrete evidence of a multi-orbital correlation driven M II in VO2. We suggest that orbital resolved electron spectroscopies can resolve this general issue of importance for transition-metal oxides. Based on the above analysis, we expect that only the yz zx DOS will cross E_F as T is increased above $T_{M I}$, while the xy DOS will still show insulating behavior. A detailed analysis of the anisotropic optical spectra across the M I transition driven by strong changes in orbital occupation can also verify the proposed scenario [15].

The above results are also consistent with the large (bad-m etallic), linear-in-T resistivity observed in the high-T m etallic phase of VO₂. Indeed, within our DM FT treatm ent of local (multi-orbital) electronic correlations, the resistivity is expected to show a quadratic tem perature dependence for T < $T_{\rm coh}$, a lattice FL coherence scale, but a linear-in-T dependence above $T_{\rm coh}$ up to high tem peratures T ' J' $4t^2$ =U' 0:1 eV [16]. For large U=t, and near the M IT, the resistivity increases way beyond the M ott limit, and increases without saturation. In VO₂, the M IT occurs at $T_{\rm M I} = 340$ K, which is much

higher than an e ective FL coherence scale (which m ight have been visible if $T_{M \ I}$ could have been low enough). Hence, the low -T FL-like resistivity is not observed, while the linear-in-T resistivity up to T = 900 K w ithout any hint of saturation can now be identied with the incoherent local (spin-orbital) m om ent regime of the m etallic phase in a multi-band Hubbard m odel. U sing this analogy, we also see that the optical conductivity w ill be alm ost com pletely incoherent in the M phase.

W e have not considered the insulating phase with spin dim erization in this communication. To do so requires an explicit consideration of the dynam icale ects associated with the c-axis dim erization. This requires a non-trivial extension of DM FT, and we leave it for the future.

In conclusion, we have shown how the two-uid picture of the M ott transition in VO_2 based on the LDA+DMFT (IPT) yields excellent quantitative agreement with the full one-electron spectrum in the metallic phase. Several features of the bad-metallic transport are also understandable in this picture. O rbital selective one-electron-and optical spectroscopy can conm /refute this outstanding issue that, in the nalanalysis, is a manifestation of M ott transitions driven by strong, multi-orbital electronic correlations.

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